

Amendments to the Claims:

Please cancel Claims 1-14.

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-14: (canceled)

Claim 15 (original): A method for forming an integrated circuit capacitor in a trench, comprising:

forming a trench in a semiconductor substrate;

forming a first dielectric layer in said trench;

forming a patterned polysilicon layer on said dielectric layer;

forming a metal silicide on said polysilicon layer;

forming a second dielectric layer over said metal silicide layer;

forming a conductive layer over said dielectric layer;

forming a hardmask layer over said conductive layer;

etching said hardmask layer and partially etching said conductive layer using a dry etch process; and

etching remaining conductive layer using a wet etch process.

Claim 16 (original): The method of claim 15 wherein said dry etch process used to etch said hardmask layer and partially etch said conductive layer is a two step etch process consisting essentially of a first plasma etch step and a second plasma etch step.

Claim 17 (original): The method of claim 16 wherein said first plasma etch step is a plasma etch process comprising Cl_2 , Ar, and BCl_3 .

Claim 18 (original): The method of claim 17 wherein said second plasma etch step is a plasma etch process comprising Cl_2 , Ar, BCl_3 , and N_2 .

Claim 19 (original): The method of claim 15 wherein said wet etch process is a two step etch process consisting essentially of a first wet etch step and a second wet etch step.

Claim 20 (original): The method of claim 19 wherein said first wet etch step comprises spraying a Piranha solution and a SC1 solution.

Claim 21 (original): The method of claim 20 wherein said second wet etch step comprises a SC1 megasonic process.